



● EE25 form factor

Primary Electrical Specifications @ 25°C				
S - F	INDUCTANCE F=100KHz, 4Vrms, 25°C	LEAKAGE INDUCTANCE F= 100KHz, 0.4 Vrms (SHORT SEC PIN)	DCR 25°C (Max)	TURN RATIO
3 - 1	1.05mH ± 10%	-	800 Ohm	56Ts

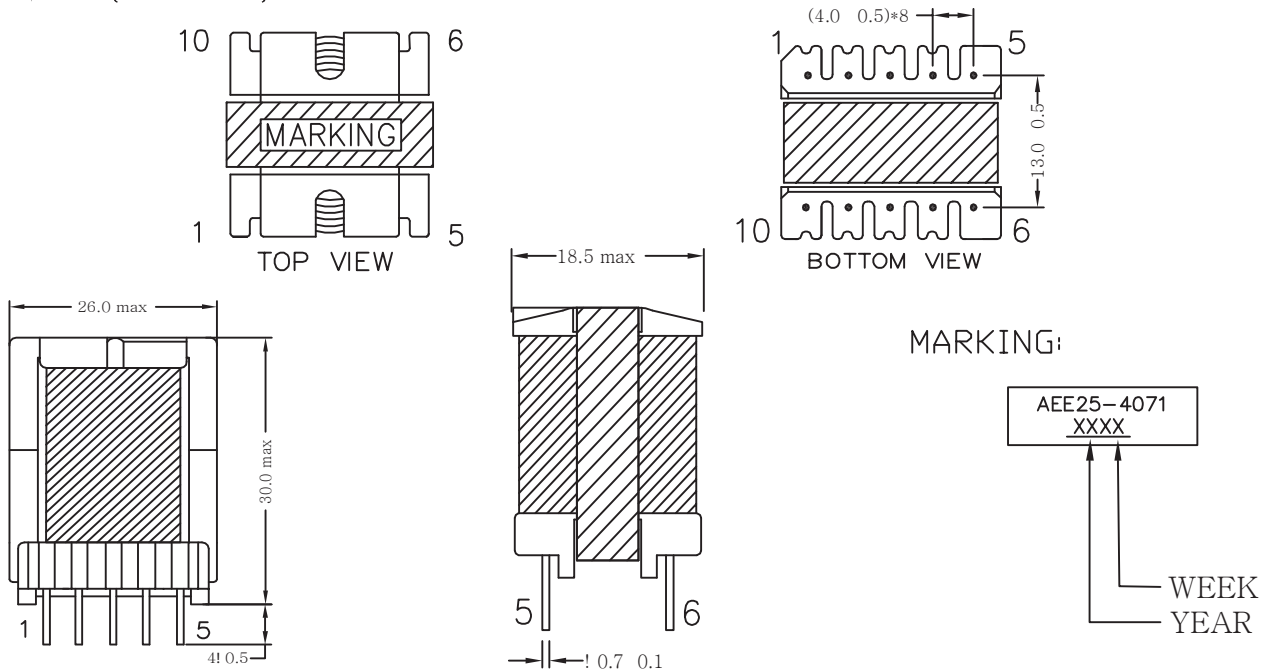
Secondary Electrical Specifications @ 25°C				
S - F	INDUCTANCE F=100KHz, 0.4 Vrms	LEAKAGE INDUCTANCE F=100KHz, 0.4 Vrms (SHORT 6,9 PINS)	DCR 25°C (Max)	TURN RATIO
4 - 5			80 mOhm	12Ts
8 - 6			50 mOhm	7Ts

Hi - Pot / Insulation Resistance					
LOCAT. \ DESC.	PRI-PRI	PRI-SEC	SEC-SEC	PRI-CORE	SEC-CORE
HI-POT (50Hz/60Hz)	-	3750Vac 5mA, 2 sec	-	2500Vac 5mA, 2 sec	2500Vac 5mA, 2 sec
INSULATION RESISTANCE	-	500Vdc 100, MOhm min	-	500Vdc 100, MOhm min	500VAC 100, MOhm min

All specifications subject to change without notice.

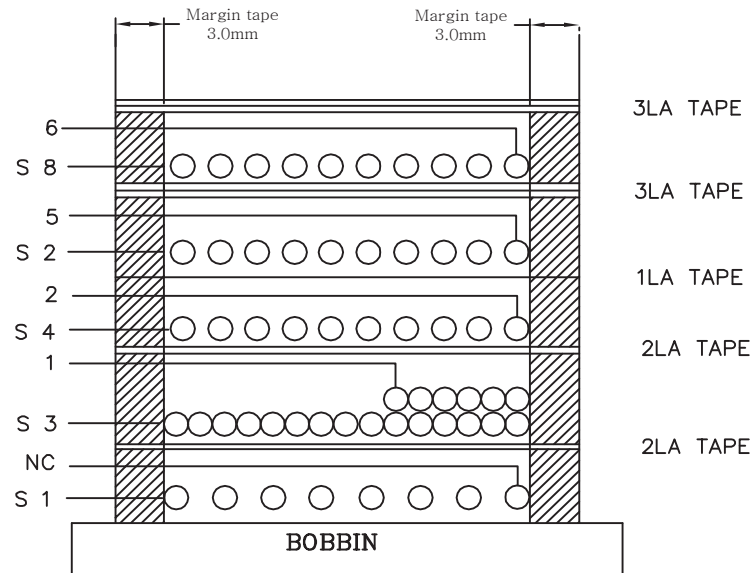
**MECHANICAL**

DIMENSION: (UNIT: mm)

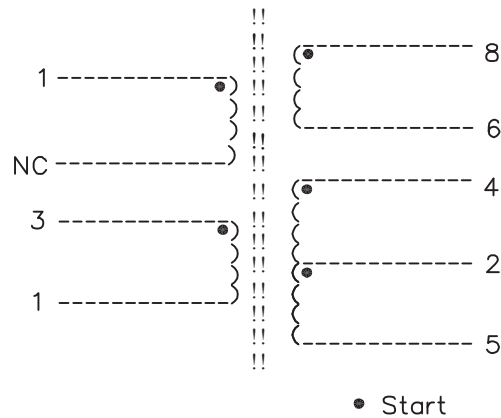




**CONSTRUCTION**



**SCHEMATICS**



**WINDING SUMMARY**

WINDING ORDER	S - F	WIRE SIZE	TURN	MARGIN TAPE	INSULATION TAPE	REMARK
#1	N1	1 - NC	14Ts	3.0mm/3.0mm	2 LAYERS	1 WIRE
#2	N2	3 - 1	56Ts	3.0mm/3.0mm	2 LAYERS	1 WIRE
#3	N3	4 - 2	6Ts	3.0mm/3.0mm	1 LAYER	1 WIRE
#4	N4	2 - 5	6Ts	3.0mm/3.0mm	3 LAYERS	1 WIRE
#5	N5	8 - 6	7Ts	3.0mm/3.0mm	3 LAYERS	1 WIRE